



Industrial microSD 6.1 Read-Only Mode (ROM) 3D TLC

A small version of the Flexxon logo, consisting of a diamond icon made of four smaller diamonds, positioned to the left of a horizontal purple line.

Version 1.0

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1. GENERAL DESCRIPTION

1.1 Introduction

The Read-Only Mode is highly effective in a memory device to ensure data security. Read-Only mode provides a tamper-proof data storage solution by making it unalterable and the crucial files remain safe.

FLEXXON Read Only Mode (ROM) microSD Card provides security function to prevent the stored data from being stolen, tampered or modified by others. Once you activate the Read-Only mode into the memory card, all the stored data enables access for reading only. None can change, delete, or overwrite anything from the stored data. So, you can preserve the authenticity of the essential files into the memory card and prohibit it from the risk of alteration. Write access could only be enabled by authorized user with specific tool and correct password.

FLEXXON ROM microSD Card plays an important role in various applications where ensuring data authenticity is extremely important. For example, in medical and healthcare facilities, financial institutes, business organizations, the cybersecurity industry, etc. will be beneficial by utilizing Read-Only Mode memory card.

The read only mode is an additional feature, which will not affect the standard product specification.

1.2 Product Overview

<ul style="list-style-type: none"> ◆ Flash 3D TLC 	<ul style="list-style-type: none"> ◆ Support SD System Specification 6.1
<ul style="list-style-type: none"> ◆ Capacity 32GB to 512GB 	<ul style="list-style-type: none"> ◆ Support SD SPI Mode
<ul style="list-style-type: none"> ◆ Support Data Crypto 	<ul style="list-style-type: none"> ◆ Support Auto Read Refreshment
<ul style="list-style-type: none"> ◆ Read disturbance management 	<ul style="list-style-type: none"> ◆ Adaptive wear leveling
<ul style="list-style-type: none"> ◆ Support management of sudden power fails 	<ul style="list-style-type: none"> ◆ SMART function support
<ul style="list-style-type: none"> ◆ Temperature Range Operation (Gold): -25°C ~ 85°C Operation (Diamond): -40°C ~ 85°C ◆ Storage: -40°C ~ 85°C 	

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1.3 Workflow

FLEXXON ROM microSD Card is a normal mode by default. User could set the password to enable read only mode by software tool.

Note: User is required to eject and re-insert the after set the password.

User could enable write access by the legal host with security tool and enter correct password. When user power off the host or reinsert the card, the card will return to read only mode.

Enable ROM Function by Software Tool and Password

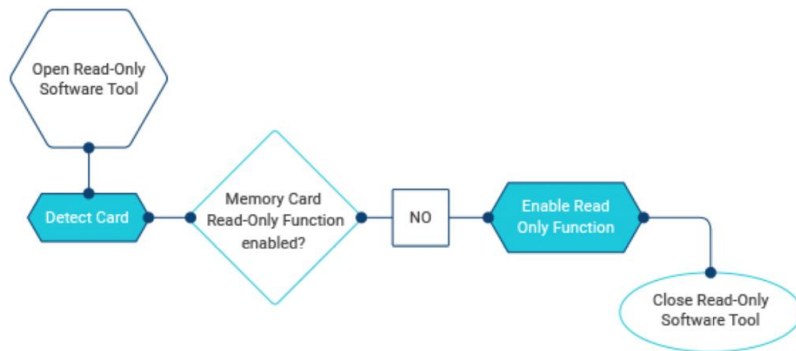


Figure 1-1: Enable ROM Function by software tool and password

Enable Write Access by software tool and password

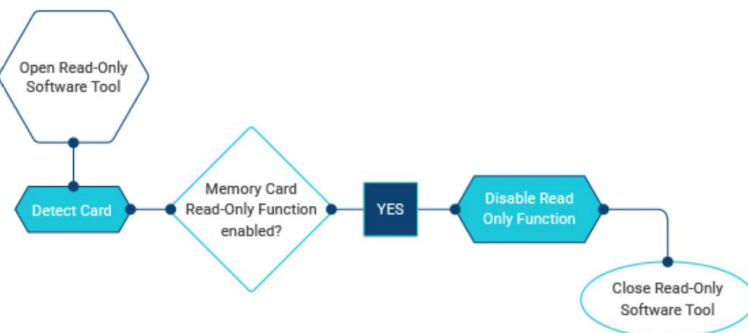


Figure 1-2: Enable Write Access by software tool and password

2. PRODUCT SPECIFICATIONS

2.1 Performance

Capacity	Sequential	
	Read (MB/s)	Write (MB/s)
32GB	85	25
64GB	85	25
128GB	85	48
256GB	85	50
512GB	85	50

Table 2-1 Performance of ROM microSD

NOTES:

1. The performance is obtained from TestMetrix
2. Performance may vary from flash configuration and platform.

2.2 Power

Capacity	Read (mA)	Write (mA)	Standby (uA)
32GB	55	42	220
64GB	62	49	200
128GB	63	73	200
256GB	64	75	220
512GB	60	75	340

Table 2-2 Typical Power Consumption of ROM microSD

2.3 MTBF

MTBF, an acronym for Mean Time Between Failures, is a measure of a device's reliability. Its value represents the average time between a repair and the next failure. The higher the MTBF value, the higher the reliability of the device. The predicted result of ROM microSD Card is more than 3,000,000 hours.

3. ENVIRONMENTAL SPECIFICATIONS

Test Items	Test Conditions
Storage Temperature	-40°C ~ 85°C
Operating Temperature	Gold: -25°C ~ 85°C Diamond: -40°C ~ 85°C
Storage Humidity	40°C, 93% RH
Operating Humidity	25°C, 95% RH
Shock	1500G, Half Sin Pulse Duration 0.5ms
Vibration	80Hz ~ 2000Hz/20G, 20Hz ~ 80Hz/1.52mm, 3 axis/30min
Drop	150cm free fall, 6 face of each unit
Bending	≥ 10N, Hold 1 min/5 times
Torque	0.1N-m or +/-2.5 deg, Hold 30 seconds/5 times
ESD	Contact: +/- 4KV each item 25 times Air: +/- 8KV 10 times

Table 3-1 Environmental Specification

4. ELECTRICAL SPECIFICATIONS

4.1 DC Characteristics

4.1.1 Bus Operation Conditions for 3.3V Signaling

Parameter	Symbol	Min.	Max	Unit	Condition
Supply Voltage	V_{DD}	2.7	3.6	V	
Output High Voltage	V_{OH}	$0.75 \cdot V_{DD}$		V	$I_{OH} = -2\text{mA}$ V_{DD} Min
Output Low Voltage	V_{OL}		$0.125 \cdot V_{DD}$	V	$I_{OL} = 2\text{mA}$ V_{DD} Min
Input High Voltage	V_{IH}	$0.625 \cdot V_{DD}$	$V_{DD} + 0.3$	V	
Input Low Voltage	V_{IL}	$V_{SS} - 0.3$	$0.25 \cdot V_{DD}$	V	
Power Up Time			250	ms	From 0V to V_{DD} min

Table 4-1 Threshold Level for High Voltage Range

Parameter	Symbol	Min.	Max	Unit	Condition
Supply Voltage	V_{DD}	2.7	3.6	V	
Regulator Voltage	V_{DDIO}	1.7	1.95	V	Generated by V_{DD}
Output High Voltage	V_{OH}	1.4	-	V	$I_{OH} = -2\text{mA}$
Output Low Voltage	V_{OL}	-	0.45	V	$I_{OL} = 2\text{mA}$
Input High Voltage	V_{IH}	1.27	2.00	V	
Input Low Voltage	V_{IL}	$V_{SS} - 0.3$	0.58	V	

Table 4-2 Threshold Level for 1.8V Signaling

Parameter	Symbol	Min	Max.	Unit	Remarks
Input Leakage Current		-2	2	μA	DAT3 pull-up is disconnected.

Table 4-3 Input Leakage Current for 1.8V Signaling

Parameter	Symbol	Min	Max.	Unit	Remarks
Peak voltage on all lines		-0.3	V _{DD} +0.3	V	
All Inputs					
Input Leakage Current		-10	10	uA	
All Outputs					
Output Leakage Current		-10	10	uA	

Table 4-4 Peak Voltage and Leakage Current

4.1.2 Bus Signal Line Load

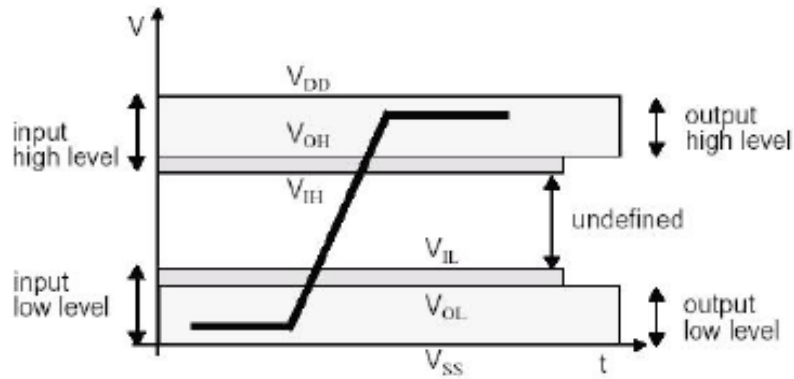
Bus Operation Conditions – Signal Line’s Load

$$\text{Total Bus Capacitance} = C_{\text{HOST}} + C_{\text{BUS}} + N C_{\text{CARD}}$$

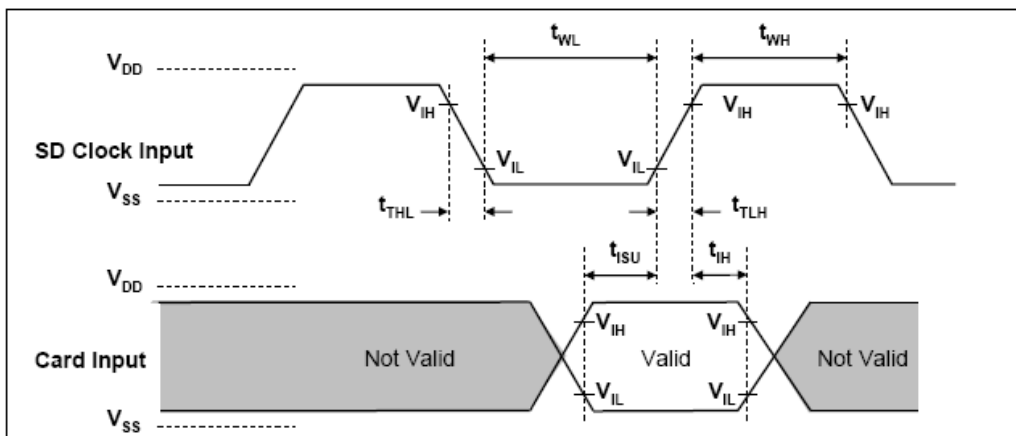
Parameter	symbol	Min	Max	Unit	Remark
Pull-up resistance	R _{CMD} R _{DAT}	10	100	kΩ	to prevent bus floating
Total bus capacitance for each signal line	C _L		40	pF	1 card C _{HOST} +C _{BUS} shall not exceed 30 pF
Card Capacitance for each signal pin	C _{CARD}		10 ¹	pF	
Maximum signal line inductance			16	nH	
Pull-up resistance inside card (pin1)	R _{DAT3}	10	90	kΩ	May be used for card detection
Capacity Connected to Power Line	C _C		5	uF	To prevent inrush current

Table 4-5 Peak Voltage and Leakage Current

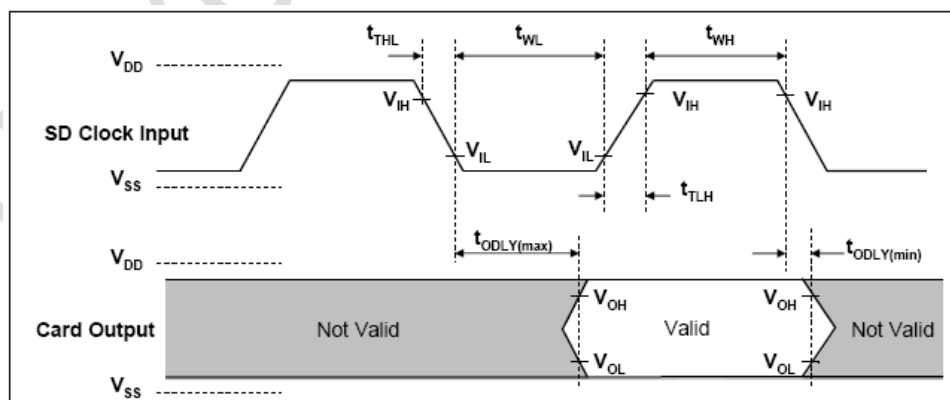
4.2 AC Characteristic



4.2.1 microSD Interface timing (Default)



Card Input Timing (Default Speed Card)

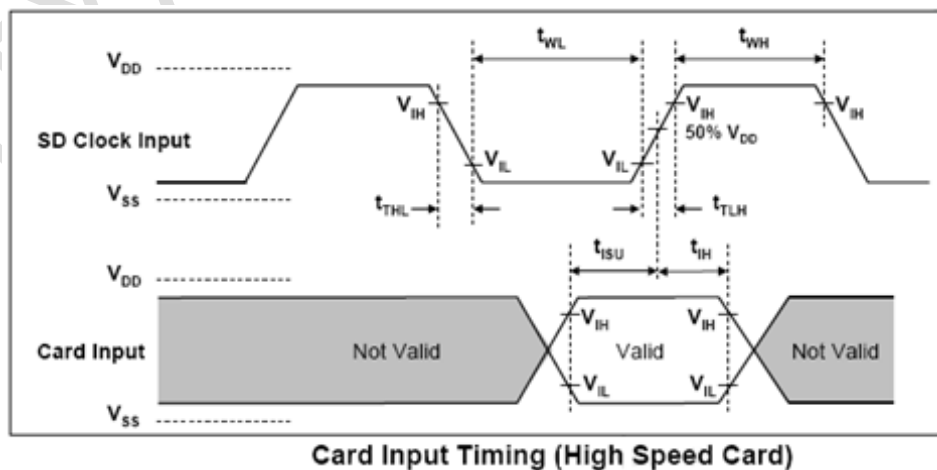


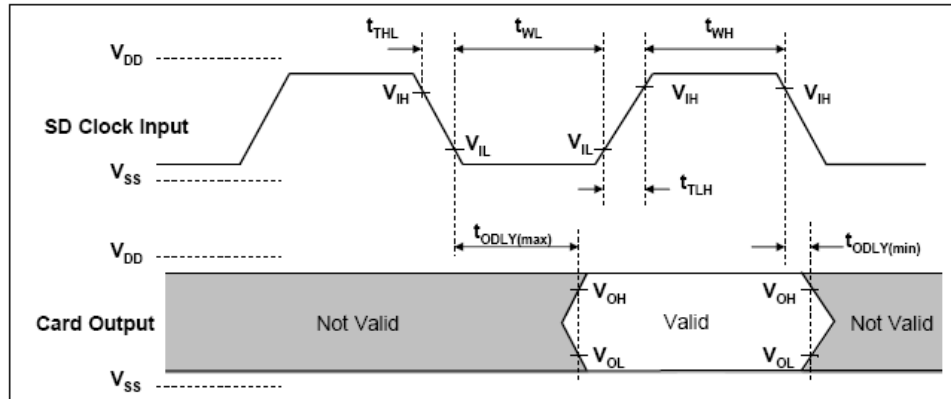
Card Output Timing (Default Speed Mode)

Parameter	Symbol	Min	Max	Unit	Remark
Clock CLK (All values are referred to min(V_{IH}) and max(V_{IL}))					
Clock frequency Data Transfer Mode	f _{PP}	0	25	MHz	C _{card} ≤ 10 pF (1 card)
Clock frequency Identification Mode	f _{OD}	0 ⁽¹⁾ /100	400	KHz	C _{card} ≤ 10 pF (1 card)
Clock low time	t _{WL}	10		ns	C _{card} ≤ 10 pF (1 card)
Clock high time	t _{WH}	10		ns	C _{card} ≤ 10 pF (1 card)
Clock rise time	t _{TLH}		10	ns	C _{card} ≤ 10 pF (1 card)
Clock fall time	t _{THL}		10	ns	C _{card} ≤ 10 pF (1 card)
Inputs CMD, DAT (referenced to CLK)					
Input set-up time	t _{ISU}	5		ns	C _{card} ≤ 10 pF (1 card)
Input hold time	t _{IH}	5		ns	C _{card} ≤ 10 pF (1 card)
Outputs CMD, DAT (referenced to CLK)					
Output Delay time during Data Transfer Mode	t _{ODLY}	0	14	ns	C _L ≤ 40 pF (1 card)
Output Delay time during Identification Mode	t _{ODLY}	0	50	ns	C _L ≤ 40 pF (1 card)

(1) 0Hz means to stop the clock. The given minimum frequency range is for cases where continues clock is required.

4.2.2 microSD Interface Timing (High-Speed Mode)





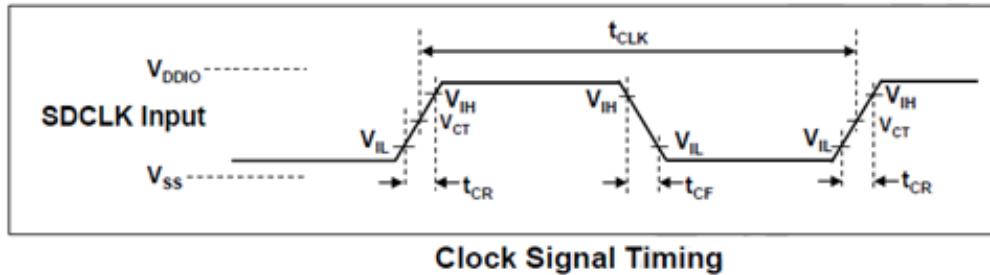
Card Output Timing (Default Speed Mode)

Parameter	Symbol	Min	Max	Unit	Remark
Clock CLK (All values are referred to min(V_{IH}) and max(V_{IL}))					
Clock frequency Data Transfer Mode	f _{PP}	0	50	MHz	C _{card} ≤ 10 pF (1 card)
Clock low time	t _{WL}	7		ns	C _{card} ≤ 10 pF (1 card)
Clock high time	t _{WH}	7		ns	C _{card} ≤ 10 pF (1 card)
Clock rise time	t _{TLH}		3	ns	C _{card} ≤ 10 pF (1 card)
Clock fall time	t _{THL}		3	ns	C _{card} ≤ 10 pF (1 card)
Inputs CMD, DAT (referenced to CLK)					
Input set-up time	t _{ISU}	6		ns	C _{card} ≤ 10 pF (1 card)
Input hold time	t _{IH}	2		ns	C _{card} ≤ 10 pF (1 card)
Outputs CMD, DAT (referenced to CLK)					
Output Delay time during Data Transfer Mode	t _{ODLY}		14	ns	C _L ≤ 40 pF (1 card)
Output Hold time	T _{OH}	2.5		ns	C _L ≤ 15 pF (1 card)
Total System capacitance of each line ¹	C _L		40	pF	C _L ≤ 15 pF (1 card)

(1) In order to satisfy severe timing, the host shall drive only one card.

4.2.3 microSD Interface timing (SDR12, SDR25, SDR50 and SDR104 Modes)

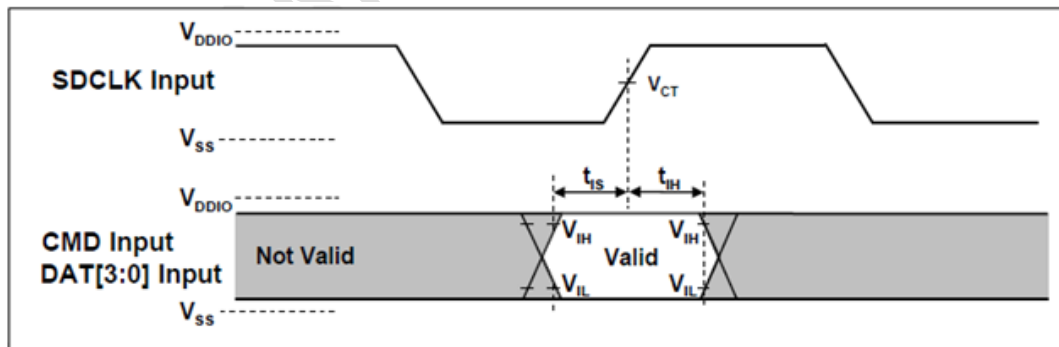
Input:



Symbol	Min	Max	Unit	Remark
t_{CLK}	4.80	-	ns	208MHz (Max.), Between rising edge, $V_{CT}=0.975V$
t_{CR}, t_{CF}	-	$0.2 * t_{CLK}$	ns	$t_{CR}, t_{CF} < 0.96ns$ (max.) at 208MHz, $C_{CARD}=10pF$ $t_{CR}, t_{CF} < 2.00ns$ (max.) at 100MHz, $C_{CARD}=10pF$ The absolute maximum value of t_{CR}, t_{CF} is 10ns regardless of clock frequency
Clock Duty	30	70	%	

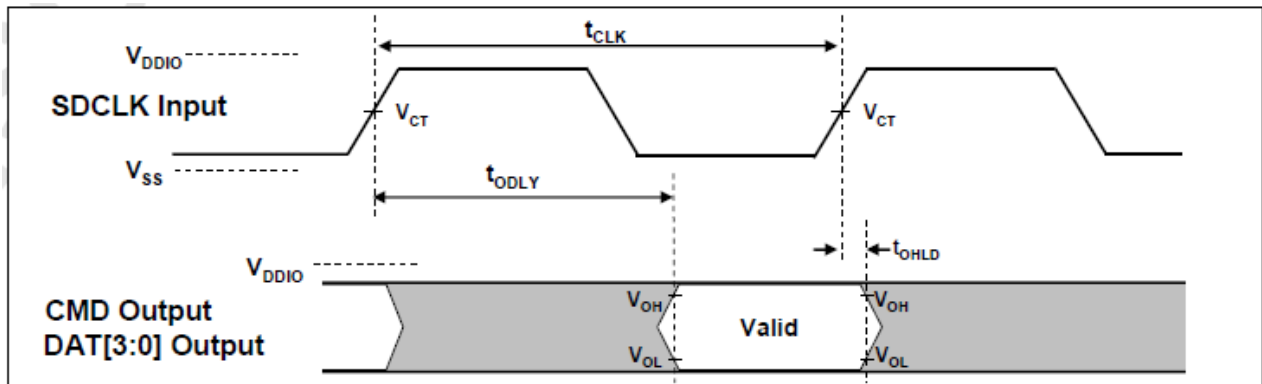
Clock Signal Timing

SDR50 and SDR104 Input Timing:



Symbol	Min	Max	Unit	SDR104 Mode
t_{IS}	1.40	-	ns	$C_{CARD} = 10pF, V_{CT} = 0.975V$
t_{IH}	0.8	-	ns	$C_{CARD} = 5pF, V_{CT} = 0.975V$
Symbol	Min	Max	Unit	SDR50 Mode
t_{IS}	3.00	-	ns	$C_{CARD} = 10pF, V_{CT} = 0.975V$
t_{IH}	0.8	-	ns	$C_{CARD} = 5pF, V_{CT} = 0.975V$

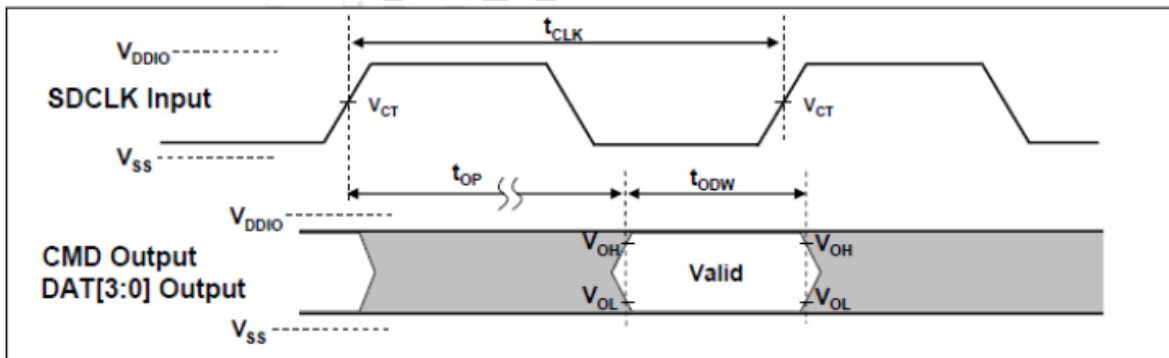
Output (SDR12, SDR25, SDR50):



Output Timing of Fixed Data Window

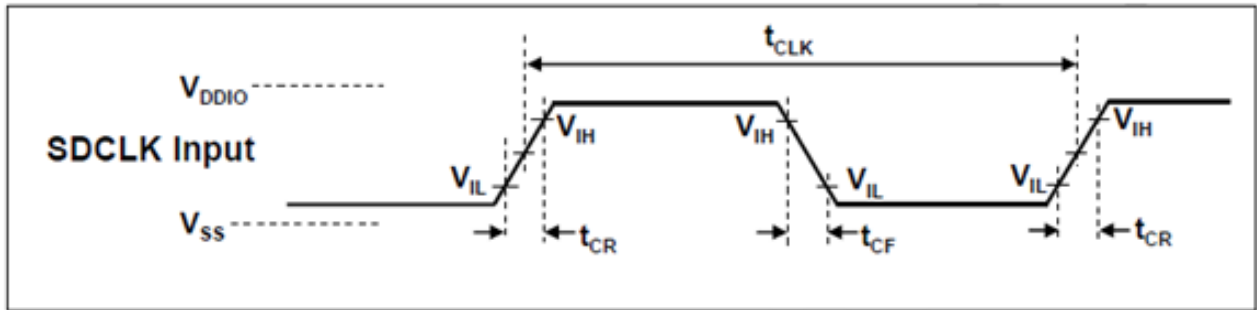
Symbol	Min	Max	Unit	Remark
t_{ODLY}	-	7.5	ns	$t_{CLK} \geq 10.0ns$, $C_L = 30pF$, using driver Type B, for SDR50
t_{ODLY}	-	14	ns	$t_{CLK} \geq 20.0ns$, $C_L = 40pF$, using driver Type B, for SDR25 and SDR12,
T_{OH}	1.5	-	ns	Hold time at the t_{ODLY} (min.), $C_L = 15pF$

Output (SDR104 Mode):



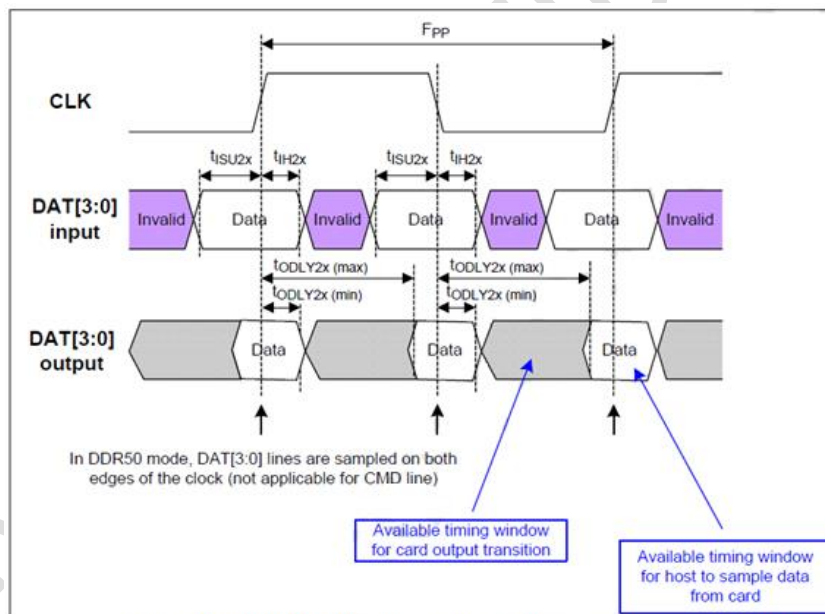
Symbol	Min	Max	Unit	Remark
t_{OP}	0	2	UI	Card Output Phase
Δt_{OP}	-350	+1550	ps	Delay variable due to temperature change after tuning
t_{ODW}	0.60	-	UI	$t_{ODW} = 2.88ns$ at 208MHz

4.2.4 microSD Interface timing (DDR50 Modes)



Clock Signal Timing

Symbol	Min	Max	Unit	Remark
t_{CLK}	20	-	ns	50MHz (Max.), Between rising edge
t_{CR}, t_{CF}	-	$0.2 * t_{CLK}$	ns	$t_{CR}, t_{CF} < 4.00ns$ (max.) at 50MHz, $C_{CARD}=10pF$
Clock Duty	45	55	%	

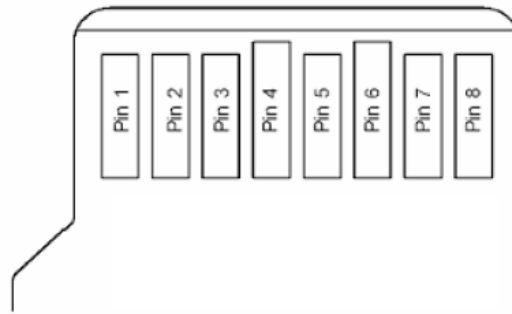


Timing Diagram DAT Inputs/Outputs Referenced to CLK in DDR50 Mode

Parameter	Symbol	Min	Max	Unit	Remark
Input CMD (referenced to CLK rising edge)					
Input set-up time	t_{ISU}	3	-	ns	$C_{card} \leq 10$ pF (1 card)
Input hold time	t_{IH}	0.8	-	ns	$C_{card} \leq 10$ pF (1 card)
Output CMD (referenced to CLK rising edge)					
Output Delay time during Data Transfer Mode	t_{ODLY}		13.7	ns	$C_L \leq 30$ pF (1 card)
Output Hold time	T_{OH}	1.5	-	ns	$C_L \geq 15$ pF (1 card)
Inputs DAT (referenced to CLK rising and falling edges)					
Input set-up time	t_{ISU2x}	3	-	ns	$C_{card} \leq 10$ pF (1 card)
Input hold time	t_{IH2x}	0.8	-	ns	$C_{card} \leq 10$ pF (1 card)
Outputs DAT (referenced to CLK rising and falling edges)					
Output Delay time during Data Transfer Mode	t_{ODLY2x}	-	7.0	ns	$C_L \leq 25$ pF (1 card)
Output Hold time	T_{OH2x}	1.5	-	ns	$C_L \geq 15$ pF (1 card)

Table 4-6 Bus Timings – Parameters Values (DDR50 Mode)

5. PAD ASSIGNMENT



Pin #	SD Mode			SPI Mode		
	Name	Type ¹	Description	Name	Type	Description
1	DAT2	I/O/PP	Data Line[bit2]	RSV		
2	CD/DAT3 ²	I/O/PP ³	Card Detect/ Data Line[bit3]	CS	I ³	Chip Select (neg true)
3	CMD	PP	Command/Response	DI	I	Data In
4	V _{DD}	S	Supply voltage	V _{DD}	S	Supply voltage
5	CLK	I	Clock	SCLK	I	Clock
6	V _{SS}	S	Supply voltage ground	V _{SS}	S	Supply voltage ground
7	DAT0	I/O/PP	Data Line[bit0]	DO	O/PP	Data Out
8	DAT1	I/O/PP	Data Line[bit1]	RSV		

Table 5-1 microSD Pad Assignment

NOTE:

- (1) S: power supply, I: input; O: output using push-pull drivers; PP: I/O using push-pull drivers
- (2) The extended DAT lines (DAT1-DAT3) are input on power up. They start to operate as DAT lines after SET_BUS_WIDTH command. The Host shall keep its own DAT1-DAT3 lines in input mode, as well, while they are not used. It is defined so, in order to keep compatibility to MultiMedia Cards.
- (3) At power up this line has a 50KOhm pull up enabled in the card. This resistor serves two functions: Card detection and Mode Selection. For Mode Selection, the host can drive the line high or let it be pulled high to select SD mode. If the host wants to select SPI mode it should drive the line low. For Card detection, the host detects that the line is pulled high. This pull-up should be disconnected by the user during regular data transfer period, with SET_CLR_CARD_DETECT (ACMD42) command.

6. REGISTERS

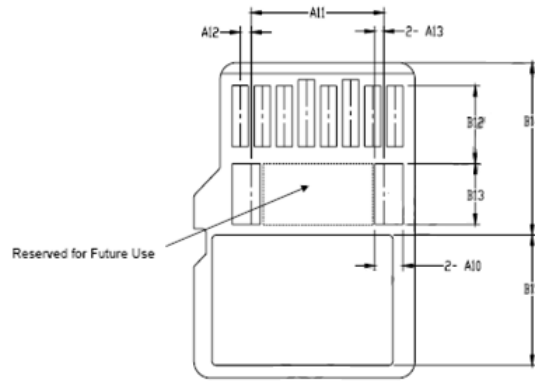
Name	Width	Description
CID	128bit	Card identification number; card individual number for identification.
RCA	16bit	Relative card address; local system address of a card, dynamically suggested by the card and approved by the host during initialization.
DSR	16bit	Driver Stage Register; to configure the card's output drivers.
CSD	128bit	Card Specific Data; Information about the card operation conditions.
SCR	64bit	SD Configuration Register; Information about the SD Memory Card's Special Features capabilities
OCR	32bit	Operation conditions register.
SSR	512bit	SD Status; Information about the card proprietary features.
OCR	32bit	Card Status; Information about the card status.

Table 6-1 microSD Registers

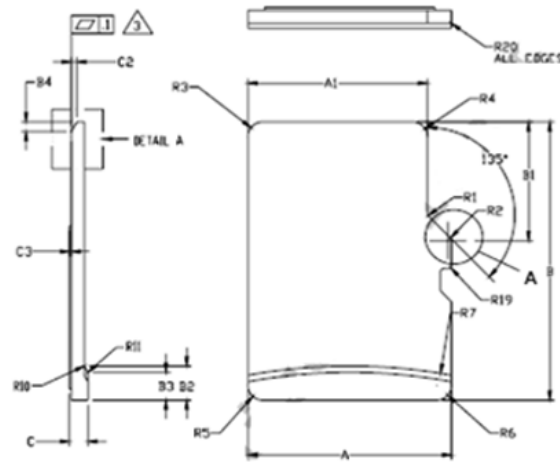
7. PHYSICAL DIMENSION

Dimension: 15mm (L) x 11mm (W) x 1mm (H)

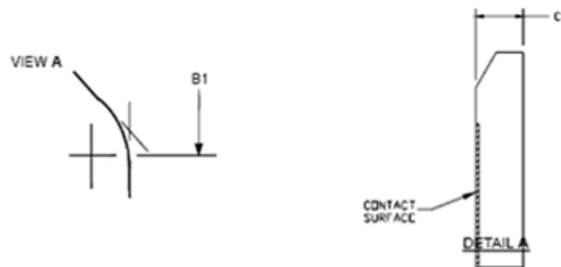
Top View



Bottom View



Side View



Common Dimensions				
Symbol	Min	Nom	Max	Note
A	10.90	11.00	11.10	
A1	9.60	9.70	9.80	
A2	-	3.85	-	Basic
A3	7.60	7.70	7.80	
A4	-	1.10	-	Basic
A5	0.75	0.80	0.85	
A6	-	-	8.50	
A7	0.90	-	-	
A8	0.60	0.70	0.80	
A9	0.80	-	-	
A10	1.35	1.40	1.45	
A11	6.50	6.60	6.70	
A12	0.50	0.55	0.60	
A13	0.40	0.45	0.50	
B	14.90	15.00	15.10	
B1	6.30	6.40	6.50	
B2	1.64	1.84	2.04	
B3	1.30	1.50	1.70	
B4	0.42	0.52	0.62	
B5	2.80	2.90	3.00	
B6	5.50	-	-	
B7	0.20	0.30	0.40	
B8	1.00	1.10	1.20	
B9	-	-	9.00	
B10	7.60	7.90	8.00	
B11	1.10	1.20	1.30	
B12	3.60	3.70	3.80	
B13	2.80	2.90	3.00	
B14	8.20	-	-	
B15	-	-	6.20	
C	0.90	1.00	1.10	
C1	0.60	0.70	0.80	
C2	0.20	0.30	0.40	
C3	-	-	0.15	
D1	1.00	-	-	
D2	1.00	-	-	
D3	1.00	-	-	
R1	0.20	0.40	0.60	
R2	0.20	0.40	0.60	
R3	0.70	0.80	0.90	
R4	0.70	0.80	0.90	
R5	0.60	0.80	0.90	
R6	0.60	0.80	0.90	
R7	29.50	30.00	30.50	
R10	-	0.20	-	
R11	-	0.20	-	
R17	0.10	0.20	0.30	
R18	0.20	0.40	0.60	
R19	0.05	-	0.20	
R20	0.02	-	0.15	

Notes:

1. Dimensioning and tolerancing per ASME Y14.5M-1994
2. Dimensions are in millimeters.
3. Coplanarity is additive to C1 Max. thickness

8. ORDERING INFORMATION

Capacity	MPN (Diamond Grade)	MPN (Gold Grade)
32GB	FDMM032GBE-XR00	FDMM032GBG-XR00
64GB	FDMM064GBE-XR00	FDMM064GBG-XR00
128GB	FDMM128GBE-XR00	FDMM128GBG-XR00
256GB	FDMM256GBE-XR00	FDMM256GBG-XR00
512GB	FDMM512GBE-XR00	-

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REVISION HISTORY

Revision	Date	History
1.0	2023/09	First Release

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